



Si Photo Diode Chip--ORT2160PD

1. Scope:

- The specification applies to NIP silicon photo-diode chips.
- Type: ORT2160PD

2. Structure:

- NIP planar type.
- Top (Cathode) Side: aluminum(Al) alloy.
- Back (Anode) Side: silver(Ag) alloy.

3. Size: (60mil×60mil)

- Chip size : 1520μm × 1520μm ± 30μm
- Chip thickness : 300μm ± 25μm
- Active area : 1350μm × 1350μm ± 15μm
- Pad size : 250μm × 250μm ± 10μm
- Pattern drawing: per fig. 1

4. Electro-Optical Characteristics:

(Ta=+25℃)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward voltage	V _F	I _F =10mA, H=0	0.5		1.3	V
Reverse Breakdown voltage	V _{BR}	I _R =100μA, H=0	35			V
Reverse Dark Current	I _D	V _R =10V, H=0			10	nA
Light Current	I _L	V _R =5V, Has 1mw/cm ² , @ 940nm		80		μA
Peak Sensing wavelength	λ _p			940		nm
Junction Capacitance	C _J	V _R =3V, F=1MHz		12		pF

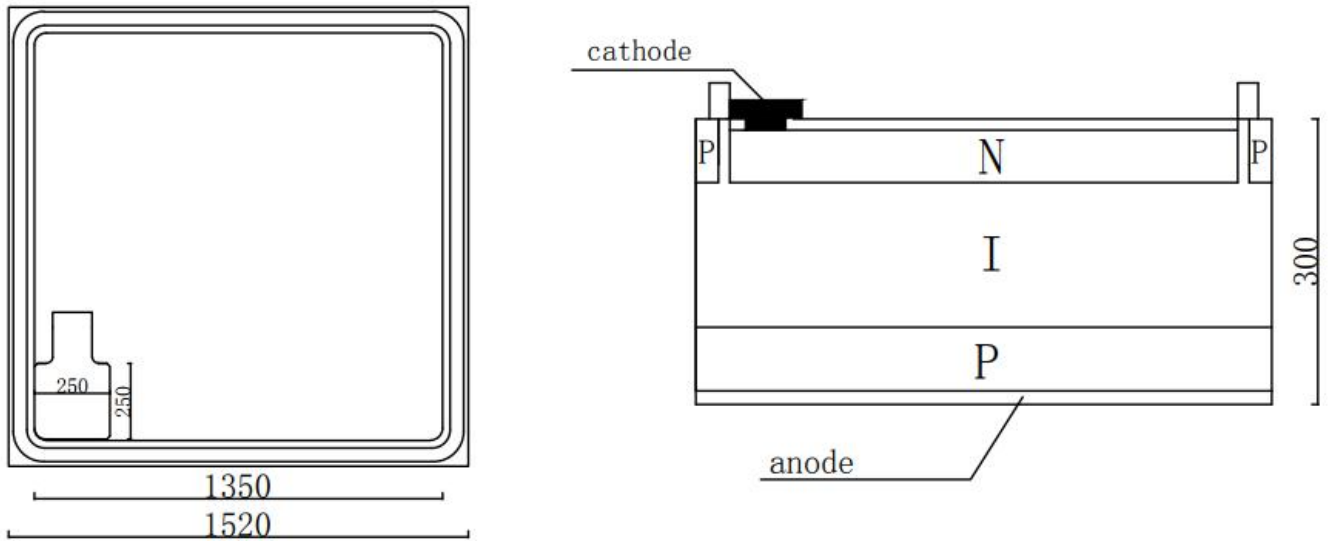


fig.1

5. Spectral Response

